

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. - 14. (canceled).

15. (currently amended): A method for producing a Group III nitride semiconductor light-emitting device having an n-type contact layer, a light-emitting layer and a p-type contact layer on a substrate, wherein the method comprises, during lowering temperature after completion of growth of the p-type contact layer composed of AlGaN containing a p-type dopant,

immediately after the completion of the growth, starting, at a temperature at which the growth has been completed, supply of a carrier gas composed of an inert gas and reduction of ~~the~~ a flow rate of a nitrogen source, wherein the flow rate of the nitrogen source after the reduction is 0.001% to 10% with respect to a flow rate of the total volume of gas; and

stopping supply of the nitrogen source at 700°C to 950°C in the course of lowering temperature.

16. (previously presented): A production method according to claim 15, wherein the temperature when the growth has been completed is 900°C or higher.

17. (previously presented): A production method according to claim 15, wherein the nitrogen source is ammonia gas.

18. (currently amended): A production method according to claim 15, wherein ~~the a~~  
carrier gas employed during growth of the semiconductor contains hydrogen gas.

19.-23. (canceled).